

The 21<sup>st</sup> Korean Conference on Semiconductors  
**제21회 한국반도체학술대회**  
February 24–26, 2014 / Hanyang University, Seoul, Korea

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F. Silicon Device and Integration Technology 분과

**[WG2-F] Fin FETs, CIS and Power Devices**

<b>Date</b>	Feb. 26, 2014 (Wed.)
<b>Place</b>	Room G / 제1공학관 405호 (# 405, Engineering Building I)

Session Chair: 이종호 교수(서울대학교), 이병훈 교수(GIST)

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- WG2-F-1**    **13:05-13:35**    **Performance Optimization Study of FinFETs Considering Parasitic Capacitance and Resistance**  
저자: SoYoung Kim  
소속: Department of Semiconductor Systems Engineering, Sungkyunkwan University
- WG2-F-2**    **13:35-13:50**    **Effect of Hydrogen Induced Gettering on Sensing Margin Enhancement of Si CMOS Image-Sensor Contaminated with Cu and Ni**  
저자: Il-Hwan Kim, Seung-Hyun Song, Joo-Hyeong Park, Gon-Sub Lee, and Jeon-Gun Park  
소속: Department of Electronics and Communication Engineering, Hanyang University
- WG2-F-3**    **13:50-14:05**    **Optimization of 7V to 60V Low V<sub>gs</sub> nLDMOS with Enhanced Specific On-Resistance**  
저자: Min-Woo Kim, Cheol-Ho Cho, Choul-Joo Ko, Min-Seok Kim, Hyung-Gyun Jung, Hee-Bae Lee, Sun-Kyung Bang, Han-Geon Kim, Sung-Mo Gu, Sun-Kyoung Kang, and Jung-Ho Kang  
소속: Product Integration Team, Dongbu Hitek
- WG2-F-4**    **14:05-14:20**    **Proposal of 90V Rated High-Side n-Type LDMOS Utilizing Double-Epi Process**  
저자: Joowon Park, Kwangsik Ko, Soonyeol Park, Daehoon Kim, Jina Eum, Kuemju Lee, Sekyung Oh, Sanghyun Lee, Inwook Cho, and Kyungdong Yoo  
소속: Technology Development team, SK hynix Inc.